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AT12020-21

SILICON ABRUPT VARACTOR DIODE

DESCRIPTION:

The **AT12020-21** is Designed for High Performance RF and Microwave Applications Requiring an Abrupt Variable Capacitance Characteristic.

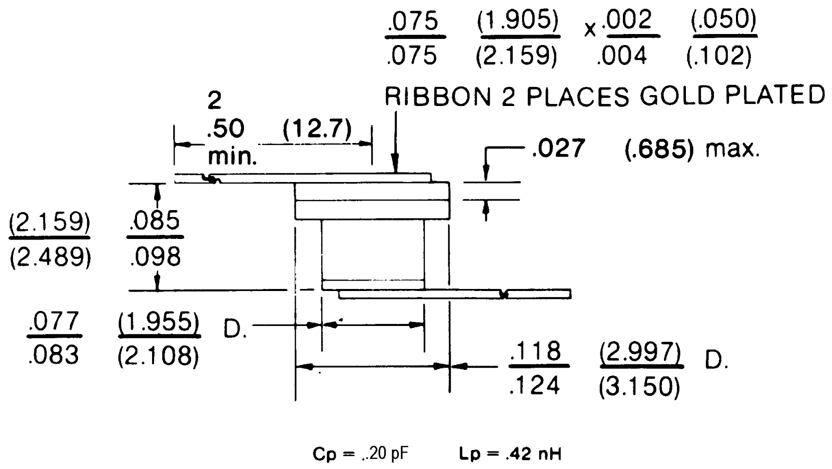
FEATURES INCLUDE:

- High Tuning Ratio, ΔC_T = **10 MIN.**
- High Quality Factor, **Q = 300 MIN.**
- Hermetic Package, **C_P = .20 pF**
  L_S = .42 nH

MAXIMUM RATINGS

I_F	200 mA
V_R	120 V
P_{DISS}	1.75W @ T_C 25 ^{O}C
T_J	-55 ^{O}C to +150 ^{O}C
T_{STG}	-55 ^{O}C to +150 ^{O}C
θ_{JC}	70 ^{O}C/W

PACKAGE STYLE 21



CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIM	UNITS
V_R	I_R = 10 µA		120			V
V_F	I_F = 1 mA				1.0	V
I_R	V_R = 100 V				100	µA
C_T	V_R = 4 V	f = 1.0 MHz	36	38	40	pF
ΔC_T	C_{T0}/ C_{T120}	f = 1.0 MHz	10.0			---
Q	V_R = 4 V	f = 50 MHz	300			---
R_S	I_F = 10 mA	f = 2400 MHz			0.9	Ω

Specifications are subject to change without notice.